



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

DMBT2907A

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

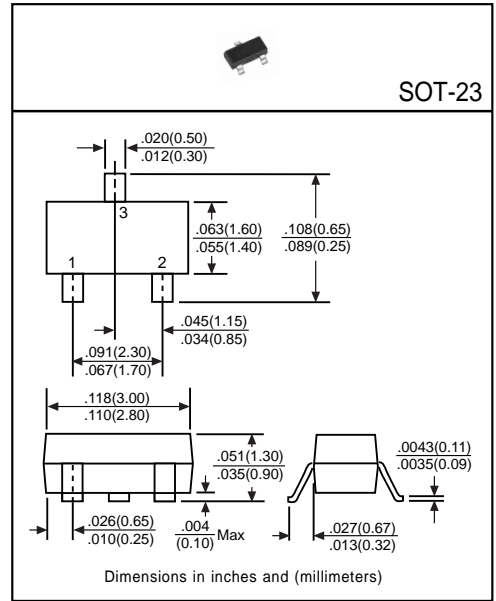
Designed for general purpose switching and amplifier applications.

Pinning

- 1 = Base
- 2 = Emitter
- 3 = Collector

Absolute Maximum Ratings (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-60	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-60	V
Emitter-Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current	I <sub>C</sub>	-600	mA
Total Power Dissipation	P <sub>D</sub>	225	mW
Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	-60	-	-	V	I <sub>C</sub> =-10μA
Collector-Emitter Breakdown Voltage	BV <sub>CE0</sub>	-60	-	-	V	I <sub>C</sub> =-10mA
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	-5	-	-	V	I <sub>E</sub> =-10μA
Collector Cutoff Current	I <sub>CBO</sub>	-	-	-20	nA	V <sub>CB</sub> =-50V
	I <sub>CEX</sub>	-	-	-50	nA	V <sub>CE</sub> =-30V, V <sub>EB(off)</sub> =-0.5V
Collector-Emitter Saturation Voltage <sup>(1)</sup>	V <sub>CE(sat)1</sub>	-	-0.2	-0.4	V	I <sub>C</sub> =-150mA, I <sub>B</sub> =-15mA
	V <sub>CE(sat)2</sub>	-	-0.5	-1.6	V	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA
Base-Emitter Saturation Voltage <sup>(1)</sup>	V <sub>BE(sat)1</sub>	-	-	-1.3	V	I <sub>C</sub> =-150mA, I <sub>B</sub> =-15mA
	V <sub>BE(sat)2</sub>	-	-	-2.6	V	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA
DC Current Gain <sup>(1)</sup>	h <sub>FE1</sub>	75	-	-	-	I <sub>C</sub> =-0.1mA, V <sub>CE</sub> =-10V
	h <sub>FE2</sub>	100	-	-	-	I <sub>C</sub> =-1mA, V <sub>CE</sub> =-10V
	h <sub>FE3</sub>	100	-	-	-	I <sub>C</sub> =-10mA, V <sub>CE</sub> =-10V
	h <sub>FE4</sub>	100	180	300	-	I <sub>C</sub> =-150mA, V <sub>CE</sub> =-10V
	h <sub>FE5</sub>	50	-	-	-	I <sub>C</sub> =-500mA, V <sub>CE</sub> =-10V
Transition Frequency	f <sub>T</sub>	200	-	-	MHz	I <sub>C</sub> =-50mA, V <sub>CB</sub> =-20V, f=100MHz
Output Capacitance	C <sub>ob</sub>	-	-	8	pF	V <sub>CB</sub> =-10V, f=1MHz, I <sub>E</sub> =0

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%